TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type (Four Darlington Power Transistors in One)

MP4104

High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

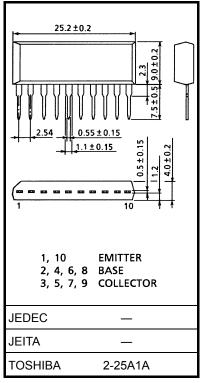
- Small package by full molding (SIP 10 pins)
- High collector power dissipation (4-device operation)
 PT = 4 W (Ta = 25°C)
- High collector current: IC(DC) = 4 A (max)
- High DC current gain: $h_{FE} = 2000$ (min) ($V_{CE} = 2$ V, $I_{C} = 1.5$ A)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	120	V	
Collector-emitter voltage		V _{CEO}	100	V	
Emitter-base voltage		V _{EBO}	6	V	
Collector current	DC	IC	4	А	
	Pulse	I _{CP}	6		
Continuous base current		ΙΒ	0.5	Α	
Collector power dissipation (1-device operation)		PC	2.0	W	
Collector power dissipation (4-device operation)		P _T	4.0	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Industrial Applications

Unit: mm

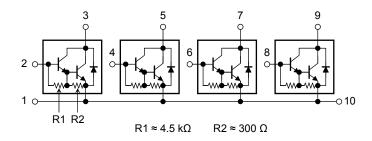


Weight: 2.1 g (typ.)

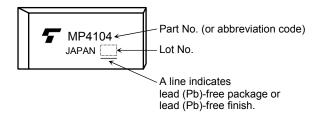
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Array Configuration



Marking



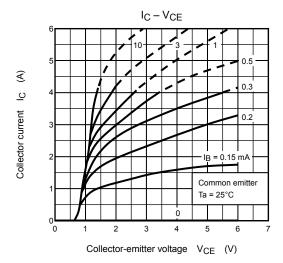
Thermal Characteristics

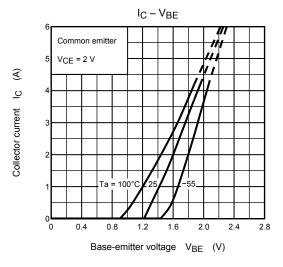
Characteristics	Symbol	Max	Unit	
Thermal resistance from junction to ambient	ΣR _{th (j-a)}	31.3	°C/W	
(4-device operation, Ta = 25°C)				
Maximum lead temperature for soldering purposes	TL	260	ů	
(3.2 mm from case for 10 s)				

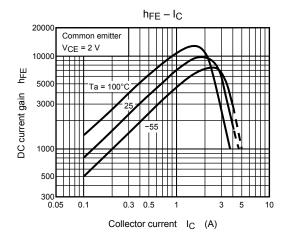
Electrical Characteristics (Ta = 25°C)

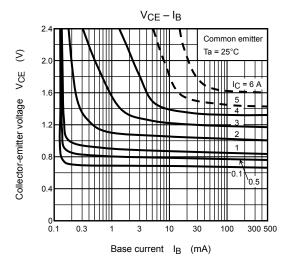
Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I _{CBO}	V _{CB} = 120 V, I _E = 0 A	_	_	10	μΑ	
Collector cut-off current		I _{CEO}	V _{CE} = 100 V, I _B = 0 A	_	_	10	μΑ	
Emitter cut-off current		I _{EBO}	V _{EB} = 6 V, I _C = 0 A	0.5	_	2.5	mA	
Collector-base breakdown voltage		V (BR) CBO	I _C = 1 mA, I _E = 0 A	120	_	_	V	
Collector-emitter breakdown voltage		V (BR) CEO	I _C = 10 mA, I _B = 0 A	100	_	_	V	
DC current gain		h _{FE (1)}	V _{CE} = 2 V, I _C = 1.5 A	2000	_	15000	_	
		h _{FE} (2)	V _{CE} = 2 V, I _C = 3.0 A	1000	_	_		
Saturation voltage	Collector-emitter	V _{CE} (sat)	I _C = 1.5 A, I _B = 3 mA	_	_	1.5	V	
	Base-emitter	V _{BE} (sat)	I _C = 1.5 A, I _B = 3 mA	_	_	2.0		
Transition frequency		f _T	V _{CE} = 2 V, I _C = 0.5 A	_	60	_	MHz	
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0 A, f = 1 MHz	_	30	_	pF	
Switching time	Turn-on time	t _{on}	Output Input $B1$ CC C	_	0.3	_		
	Storage time	t _{stg}		_	2.0	_	μs	
	Fall time	t _f		_	0.4	_		

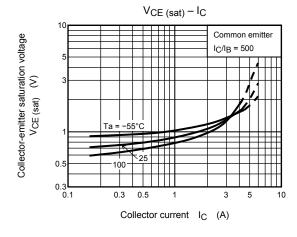
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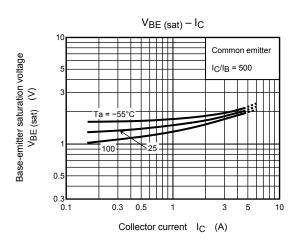


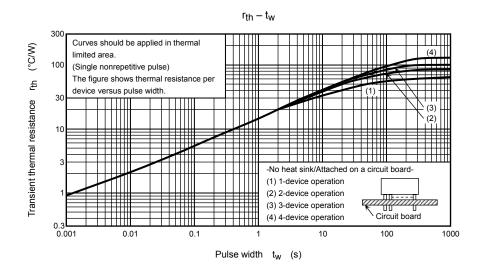


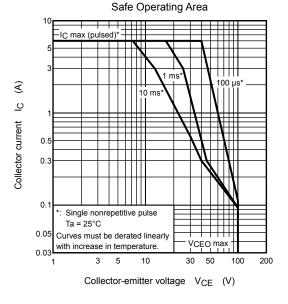


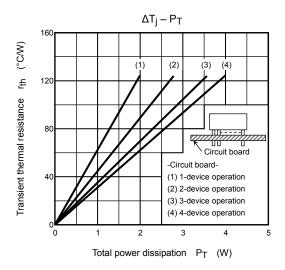


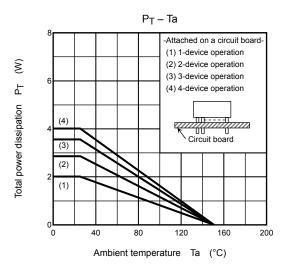












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